

Generated Document (11) Publication number:

01217956 A

## PATENT ABSTRACTS OF JAPAN

(21) Application number: 63041948

(51) Intl. Cl.: H01L 27/04 H01L 21/205

(22) Application date: 26.02.88

(30) Priority:

publication: (43) Date of application

(84) Designated contracting 31.08.89

states:

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MANUFACTURE THEREOF CONDUCTOR LAYER AND (54) CONDUCTOR LAYER, CAPACITOR USING

## (57) Abstract:

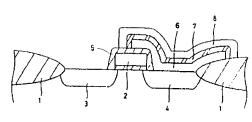
amorphous silicon containing no forming the conductor layer by using dielectric strength is increased, by electric field does not concentrate and capacitor using said layer wherein crystal grains. layer whose surface is flat, and a PURPOSE: To obtain a conductor

oxygen is used as reaction gas. Vapor growth is performed by heating the disilane or trisilane or tetrasilane and CONSTITUTION: Mixed gas of region on the amorphous layer 6. eliminated from the region except a an insulating layer 7 is formed, it is region in contact with drain 4. After quality is formed on a substrate. By amorphous silicon layer of excellent conductor layer composed of an of tetrasilane. Thus a flat surface trisilane, and 300-400°C in the case disilane, 350-450°C in the case of follows; 400-500°C in the case of above gas, and its temperature is as After a conductor layer 8 like a eliminated from the region except a MOS field effect transistor, and is subjected to vapor growth on a method, an amorphous silicon layer 6 using the above manufacturing

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conducting layer 8 is formed. composed of the amorphous silicon insulating layer 7, and a capacitor region except a region on the formed, it is eliminated from the polycrystalline silicon layer is

layer 6, the insulating layer 7 and the



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